

# Polarization effects in radiation damaged scCVD Diamond detectors

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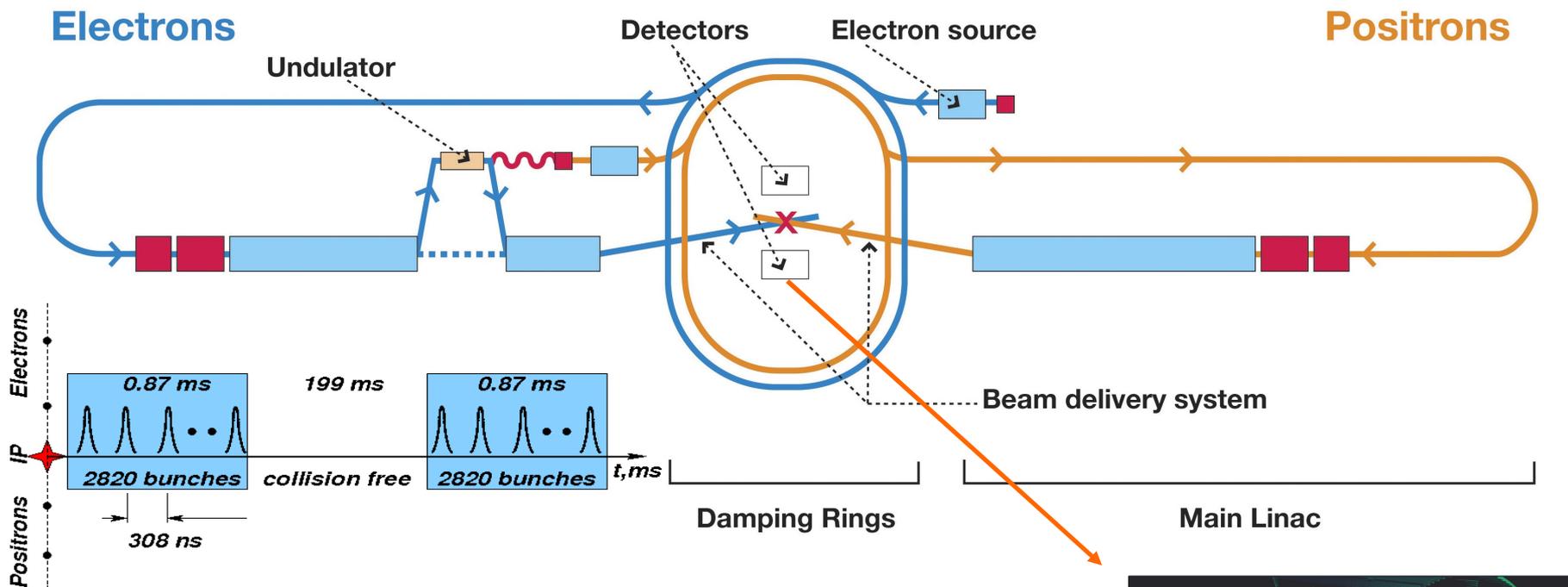
4<sup>th</sup> NoRHDia Workshop @ GSI

- Why do we need Diamond Detector @ ILC?
- BeamCal challenge
- Diamond properties
- Charge collection
  - Ideal crystal, Radiation damaged crystal
- Polarization creation, model
- Experimental studies:
  - CCD vs Dose, CCD time dependence
  - Future plans
- Summary



# The International Linear Collider

~30km



## Parameters:

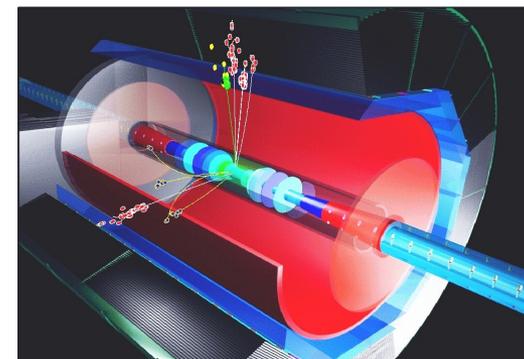
500 GeV (1 TeV upgrade possible)

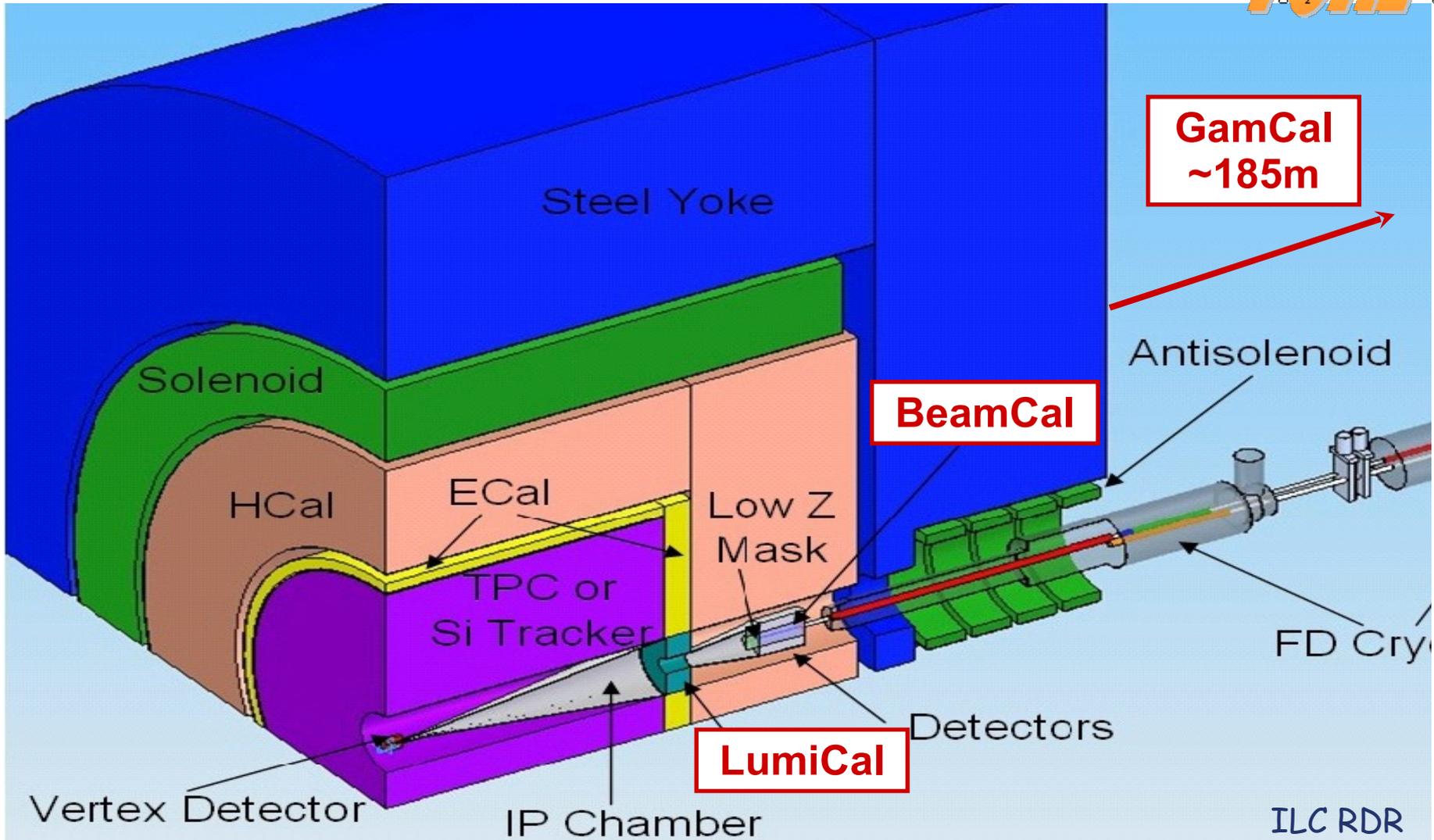
$2 \times 10^{34} \text{ cm}^{-2}\text{sec}^{-1}$

electron polarization ~80 %

positron polarization ~30 % (60 %)

beam sizes:  $\sigma_x \approx 600\text{nm}$ ,  $\sigma_y \approx 6\text{nm}$ ,  $\sigma_z = 300\mu\text{m}$





- Compact em calorimeter with sandwich structure:

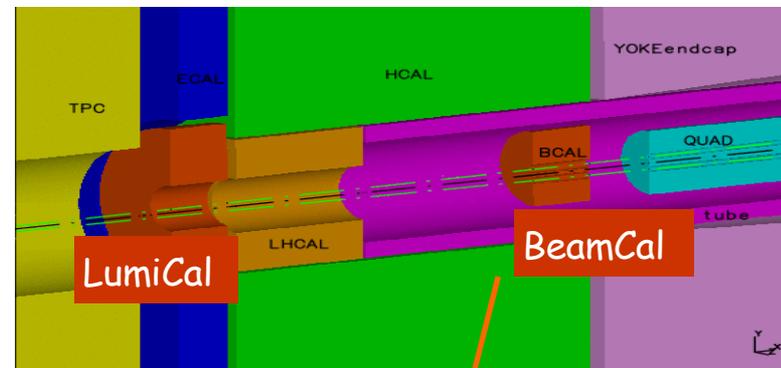
- 30 layers of  $1 X_0$

- 3.5mm W and 0.3mm sensor

- ★ Angular coverage from  $\sim 5\text{mrad}$  to  $\sim 45\text{mrad}$

- ★ Molière radius  $R_M \approx 1\text{cm}$

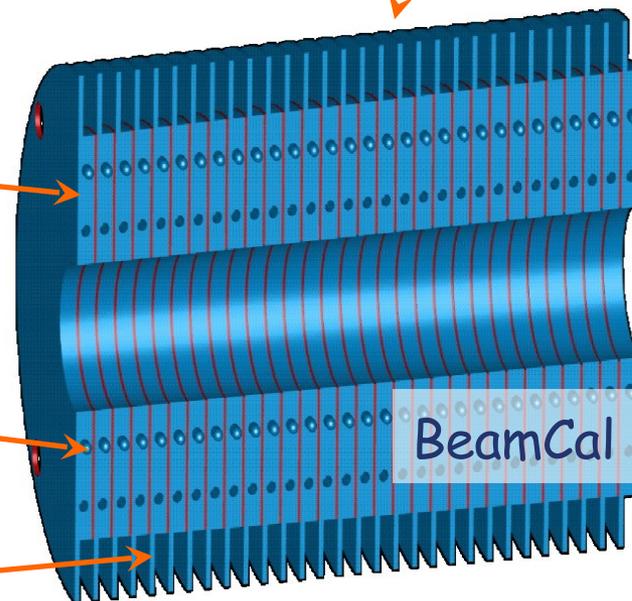
- ★ Segmentation between  $0.5$  and  $0.8 \times R_M$



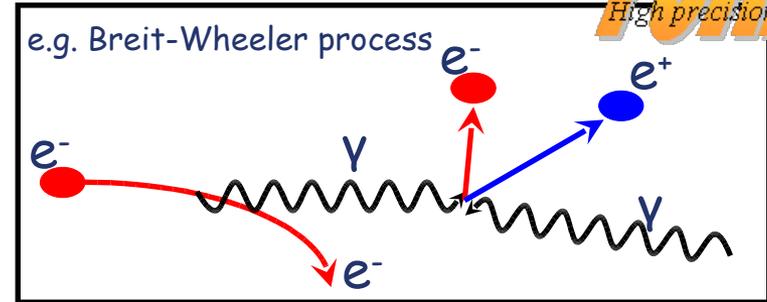
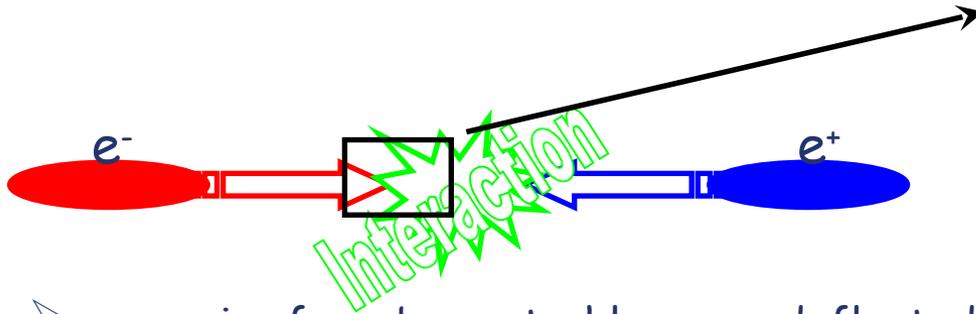
W absorber layers

Radiation hard sensors with thin readout planes

Space for readout electronics



Creation of beamstrahlung at the ILC



➤ e<sup>+</sup>e<sup>-</sup> pairs from beamstrahlung are deflected into the BeamCal

➤ 15000 e<sup>+</sup>e<sup>-</sup> per BX

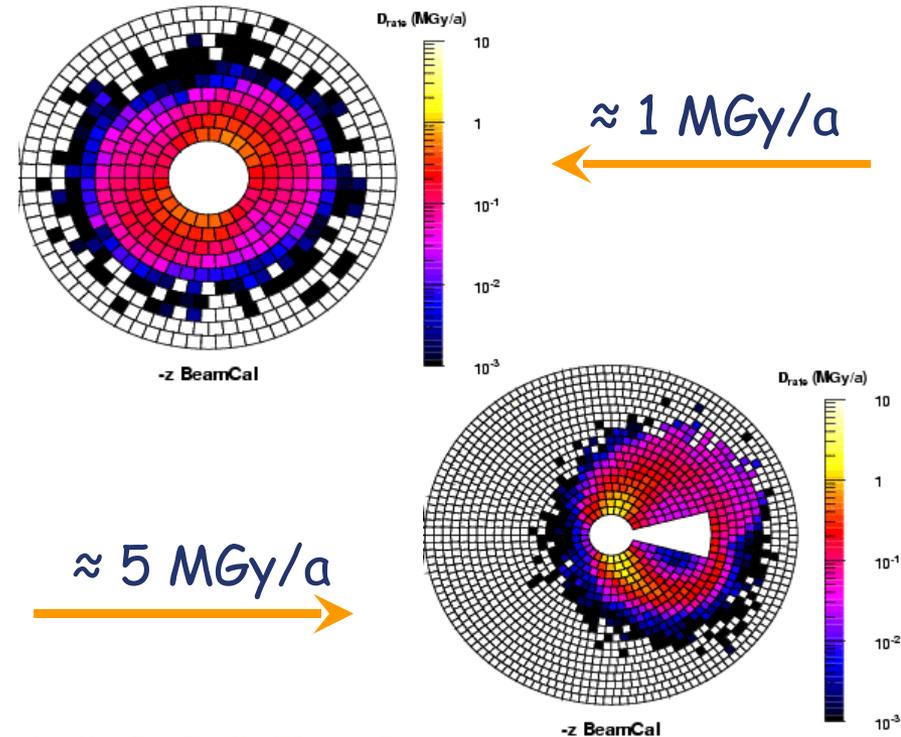
⇒ 10 - 20 TeV total energy dep.

➤ ~ 10 MGy per year strongly dependent on the beam and magnetic field configuration

⇒ radiation hard sensors

➤ Detect the signature of single high energetic particles on top of the background.

⇒ high dynamic range/linearity.



# Diamond properties

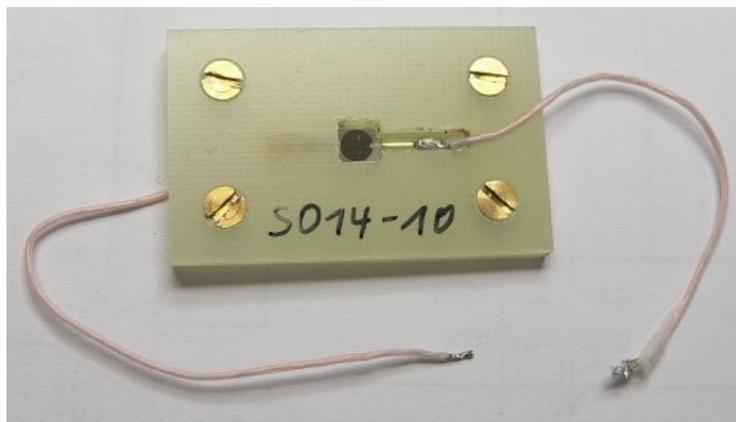
- Density  $3.52 \text{ g cm}^{-3}$
- Dielectric constant 5.7
- Breakdown field  $10^7 \text{ V cm}^{-1}$
- Resistivity  $>10^{11} \Omega \text{ cm}$
- Band Gap 5.5 eV
- Electron mobility 1800 (4500)  $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$
- Hole mobility 1200 (3800)  $\text{cm}^2 \text{ V}^{-1} \text{ s}^{-1}$
- Energy to create e-h pair 13.1 eV
- Average signal created  $36 \text{ e } \mu\text{m}^{-1}$

\* High-purity single crystal CVD

# Sensors

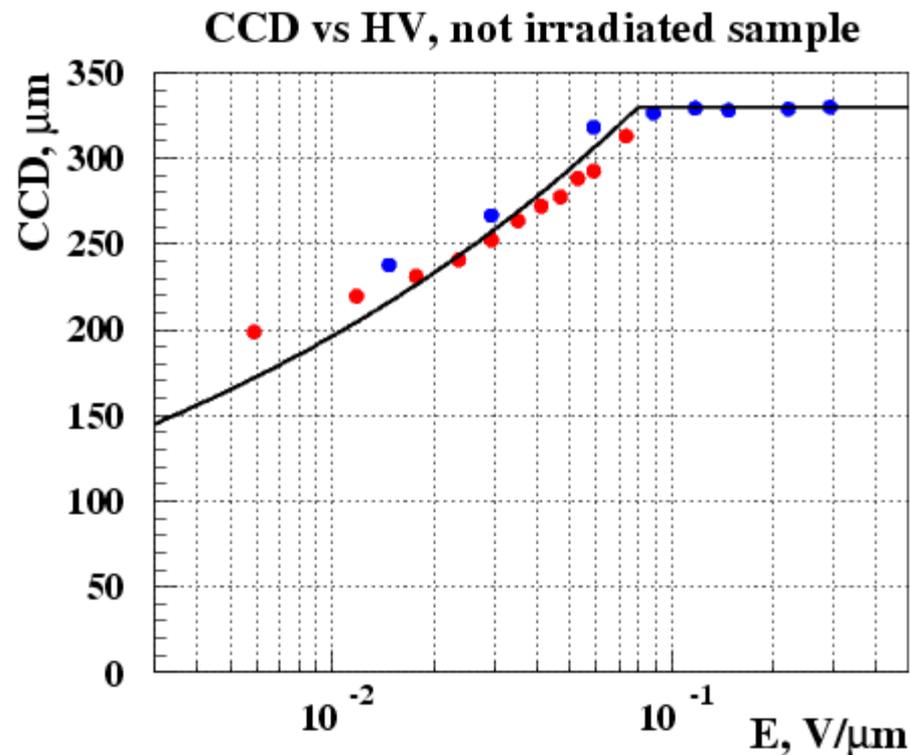
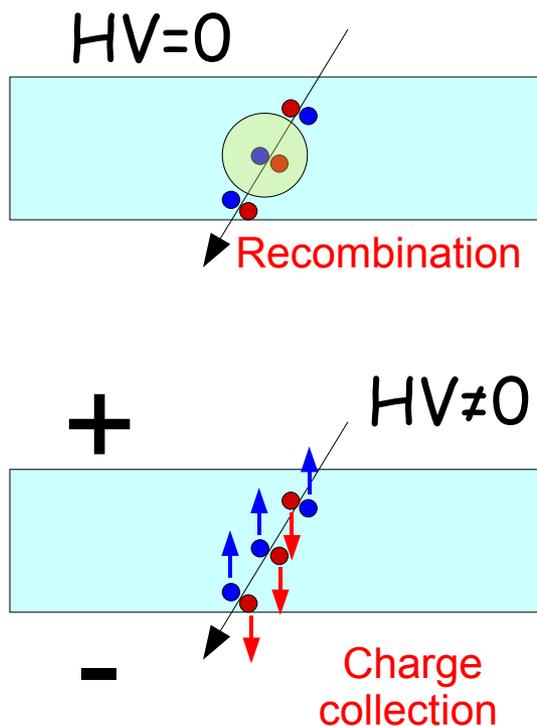
sc CVD diamond from Element 6  
(provided by GSI, Darmstadt)

Thickness 326  $\mu\text{m}$ , active area 3mm in diameter



2 sensors, one is irradiated up to 5 MGy dose  
at the 10 MeV electron beam in 2007

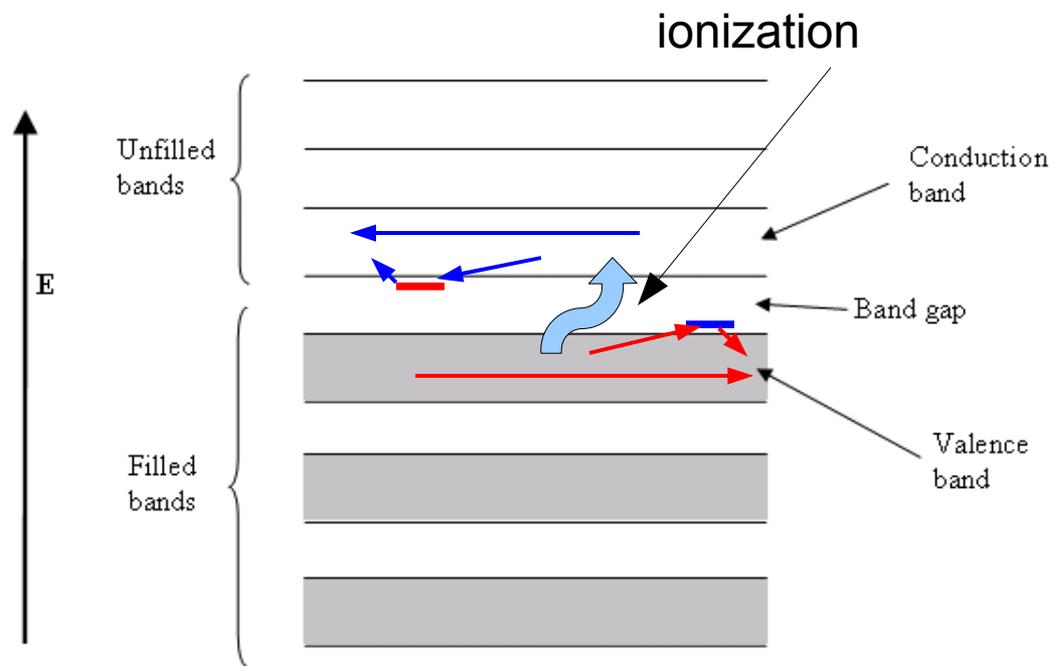
- Charge collection efficiency depends on  $E$



# Radiation damaged crystal

- Radiation causes local damages of the lattice structure.
- These local damages (traps) are able to capture free charge carriers and release them after some time

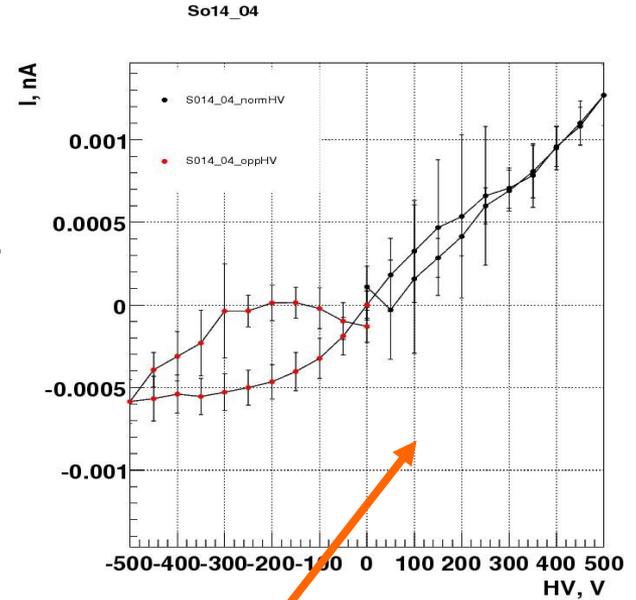
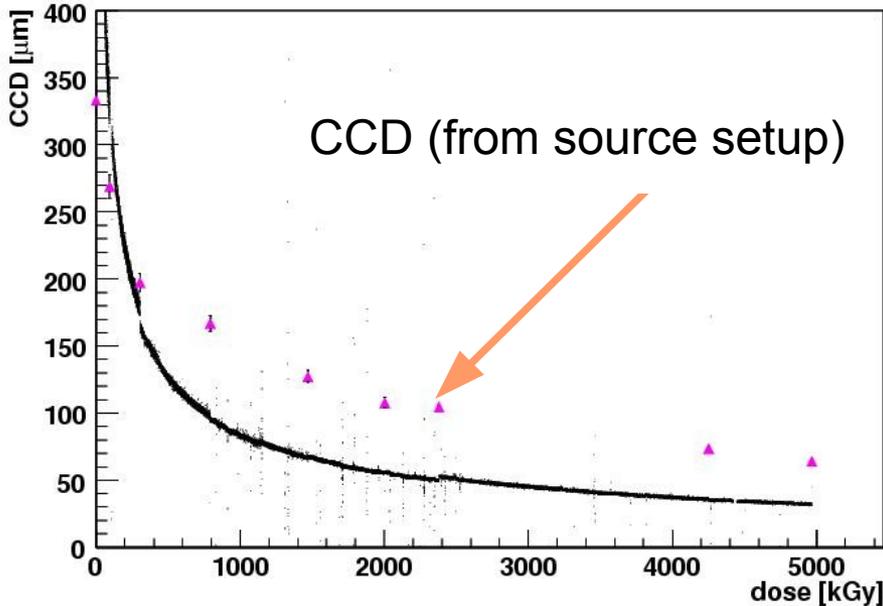
- **Assumptions:**
- **Trap density is uniform (bulk radiation damage)**
- **Traps are created independently (linearity vs dose)**



After absorbing 5 MGy:

CVD diamonds still operational.

CCD (from  $I_{sens}$ ) vs dose

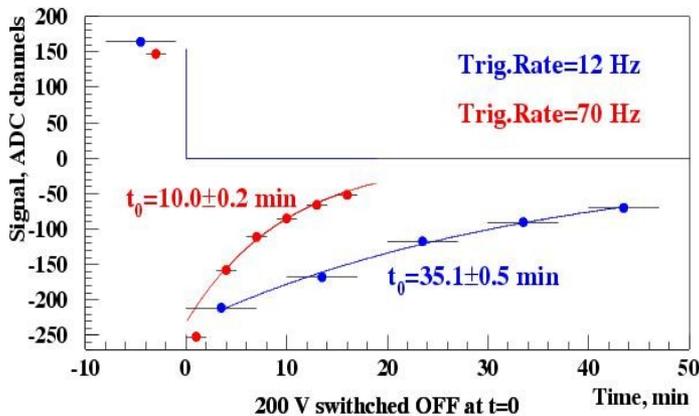
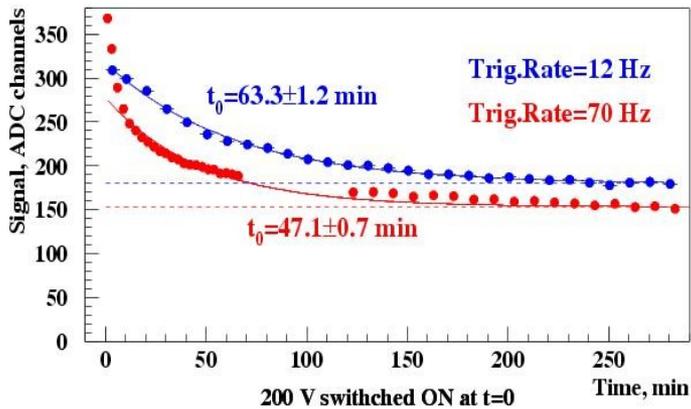


- Very low leakage currents ( $\sim$ pA) after the irradiation.
- Decrease of the charge collection distance with the dose.
- Generation of trapping centers due to irradiation. **Traps release?**
- **Strong polarization effects !!!**

After absorbing 5 MGy:

Measurements at  $^{90}\text{Sr}$ -source setup:

So14-04 Diamond Sample



After switching HV on signal drops with time

Switching HV off after signal stabilization: strong signal of opposite polarity is observed

Signal time behavior depends on the MIPs rate

**Dynamic polarization !**

## Polarization Model

Radiation damage – uniformly produced traps

MIP signal – uniformly produced e-h pairs

+Electric field → **NONUNIFORM** space charge

Change of the electric field

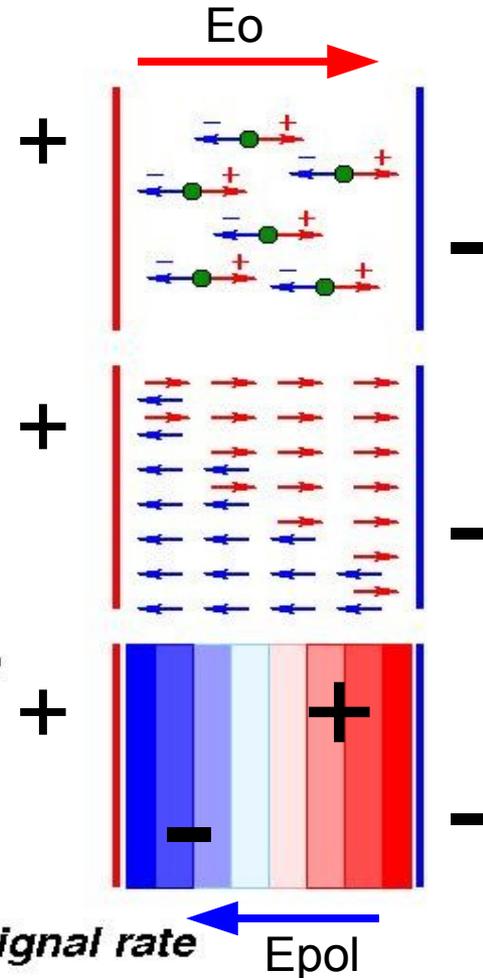
e-h Recombination if the field is low

Release of trapped charges (decay time)

Change of the space charge distribution

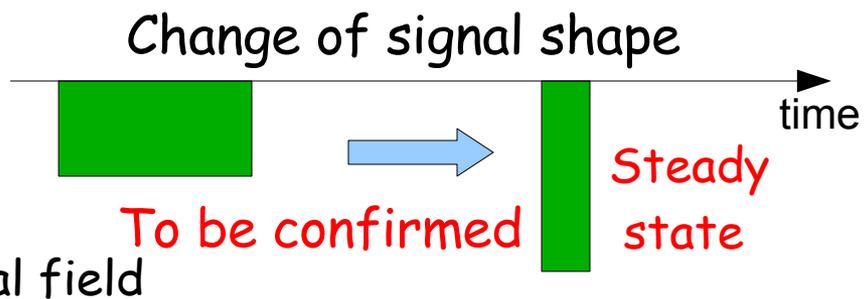
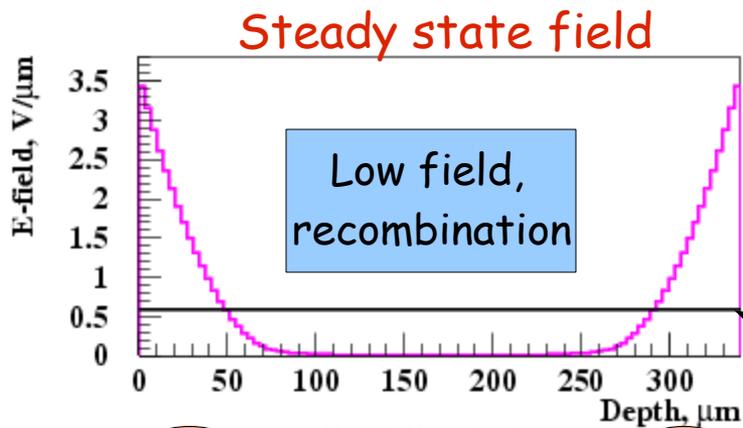
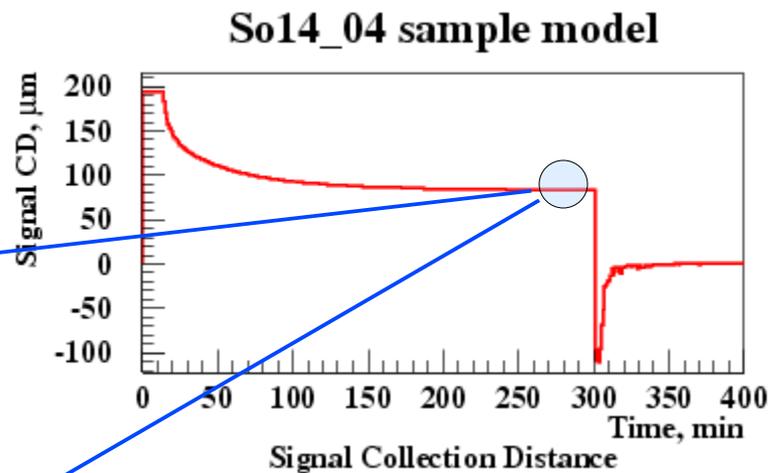
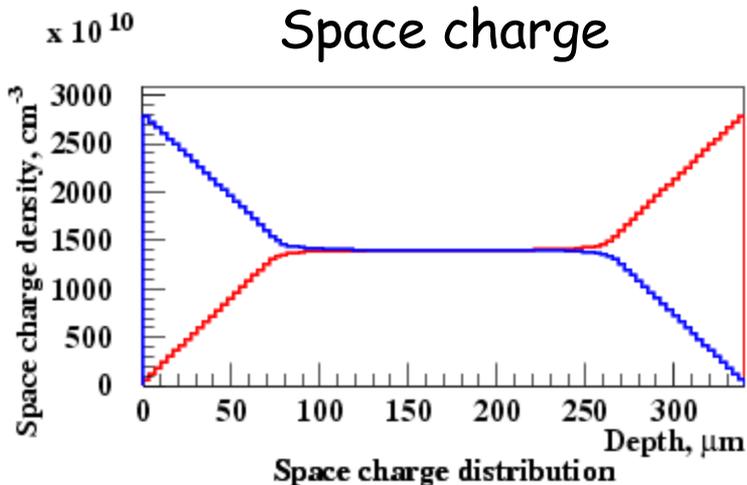
**Steady state POLARIZATION**

Dependent on trap density, applied voltage and signal rate



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# Model of sCVD Diamond Polarization - 1

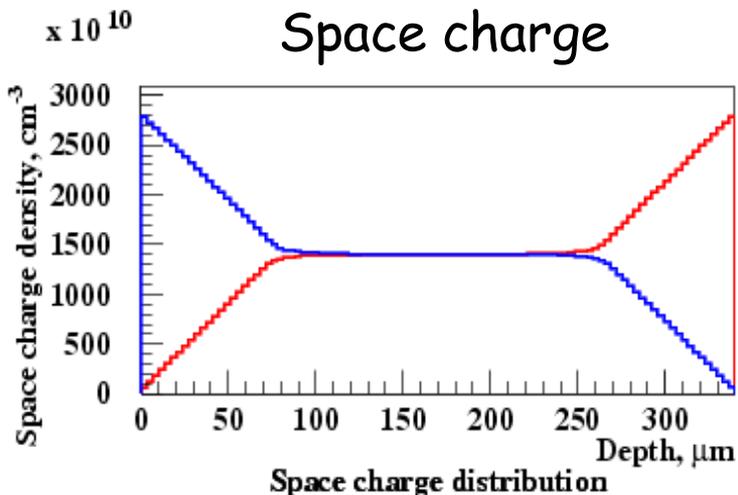


Initial field

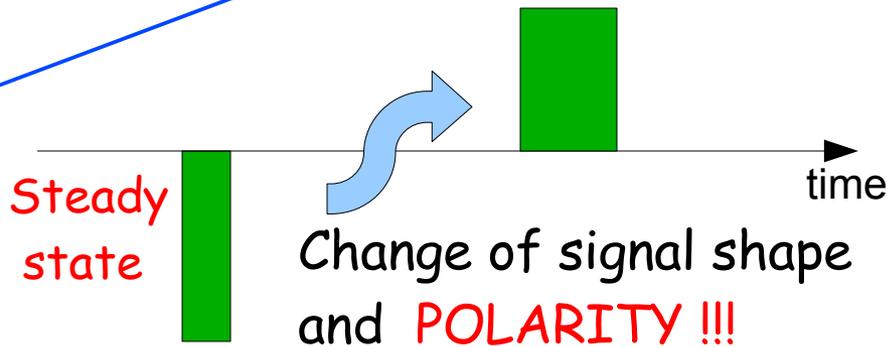
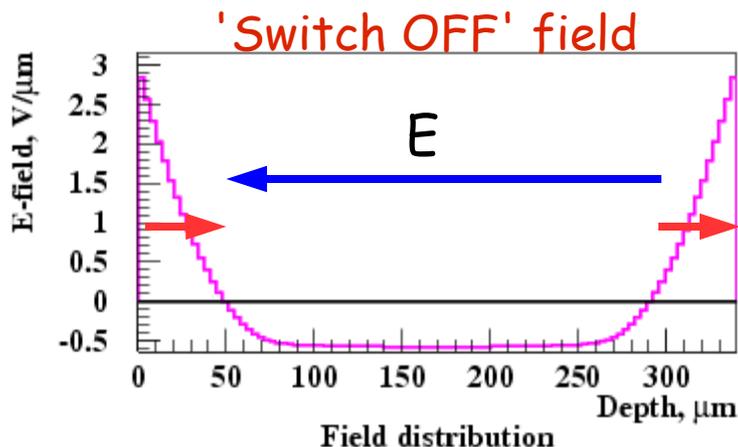
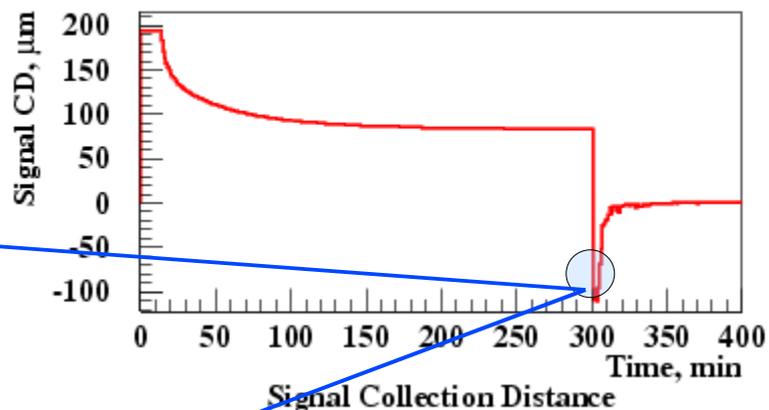
Effective charge collection regions

# Model of sCVD Diamond Polarization - 2

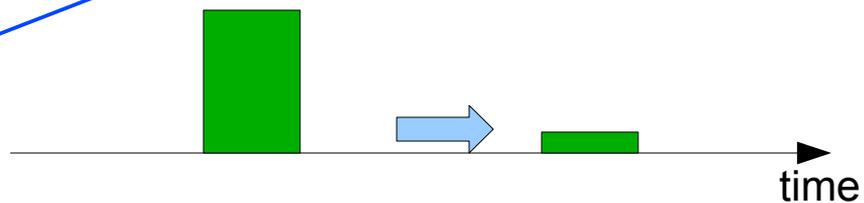
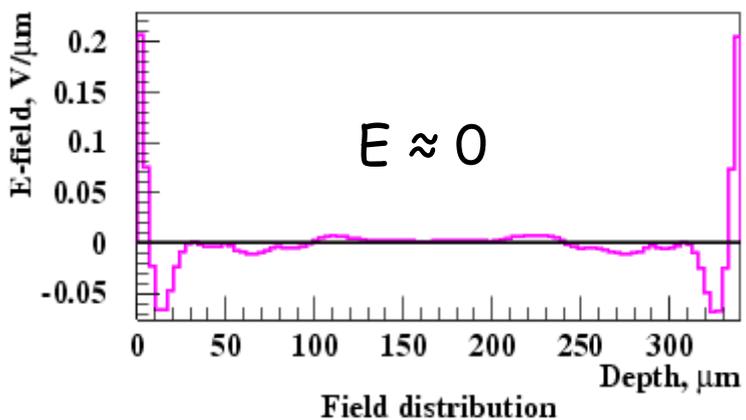
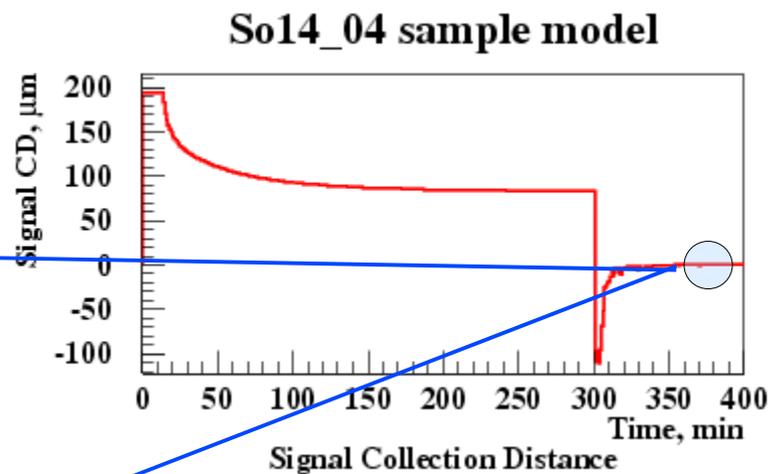
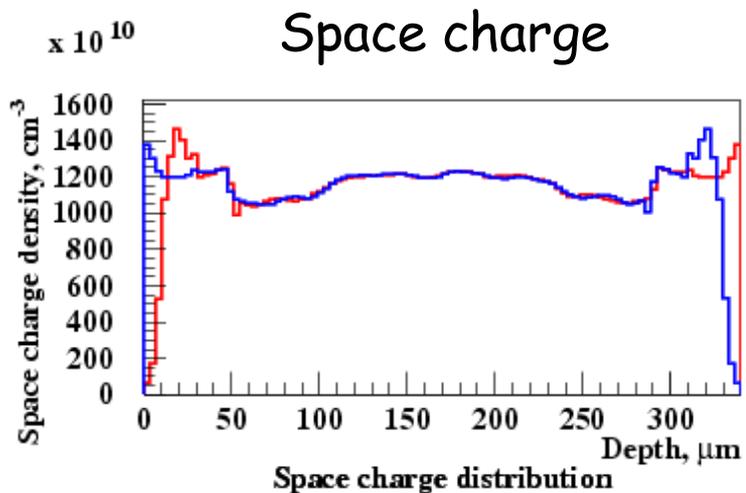
HV  $\rightarrow$  0 !



So14\_04 sample model



HV = 0





# <sup>90</sup>Sr setup: CCD time dependence

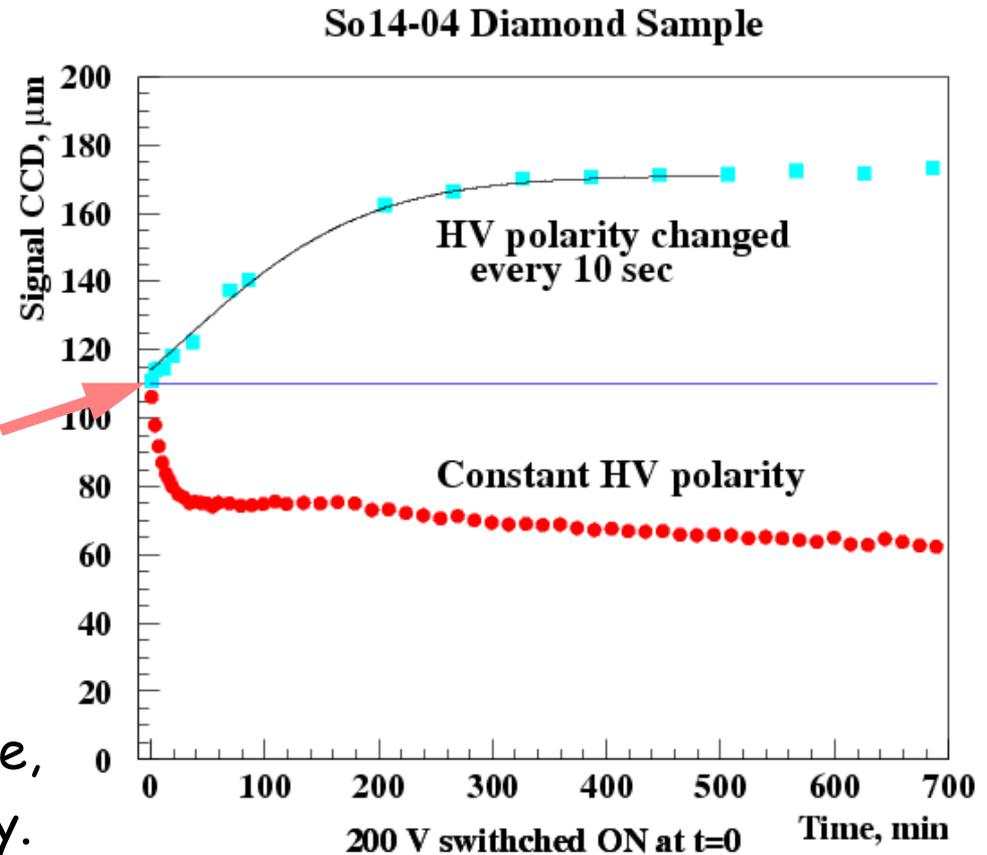
## ➤ Diamond sCVD sensor after 5 MGy

$$CCE_0 = \frac{2}{aD} \cdot \left( 1 - \frac{1 - \exp(-aD)}{aD} \right)$$
$$a = \frac{\pi R_{trap}^2}{l_0} \cdot \frac{n_{free}}{N}$$

CCD at t=0 allows  
to extract  $n_{trap} R_{trap}^2$  value

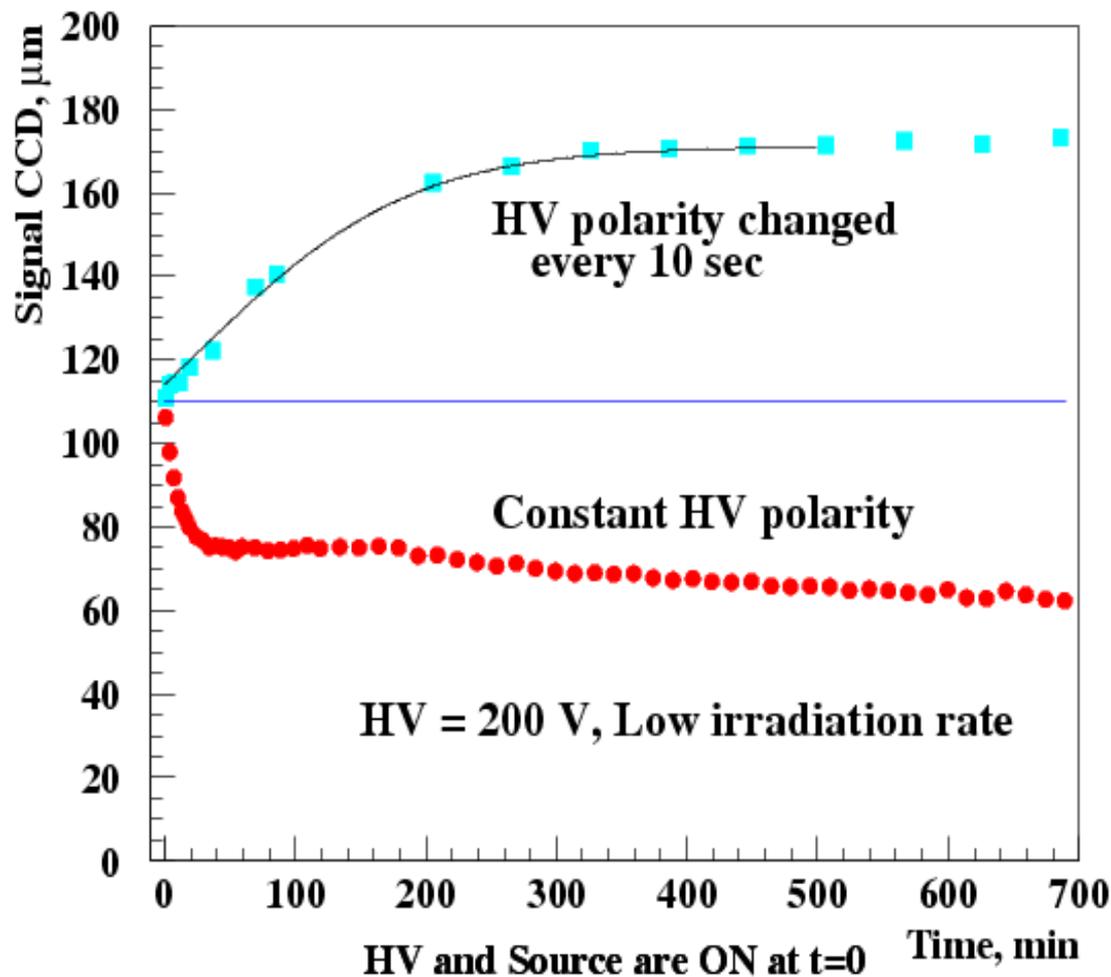
Steady state CCD is sensitive  
to  $n_{trap}$ ,  $T_0$  and signal rate

Curve shape depends on the rate,  
trap properties and trap density.

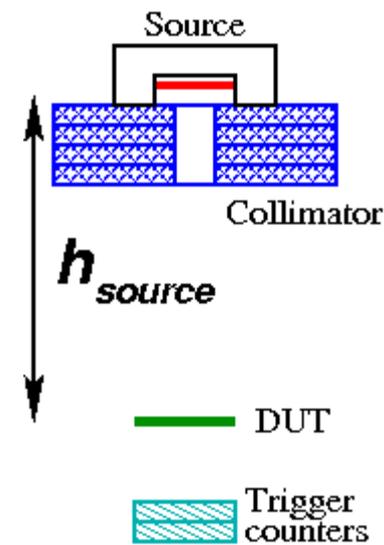


# CCD vs time dependence, low rate

So14-04 Diamond Sample (5 MGy)

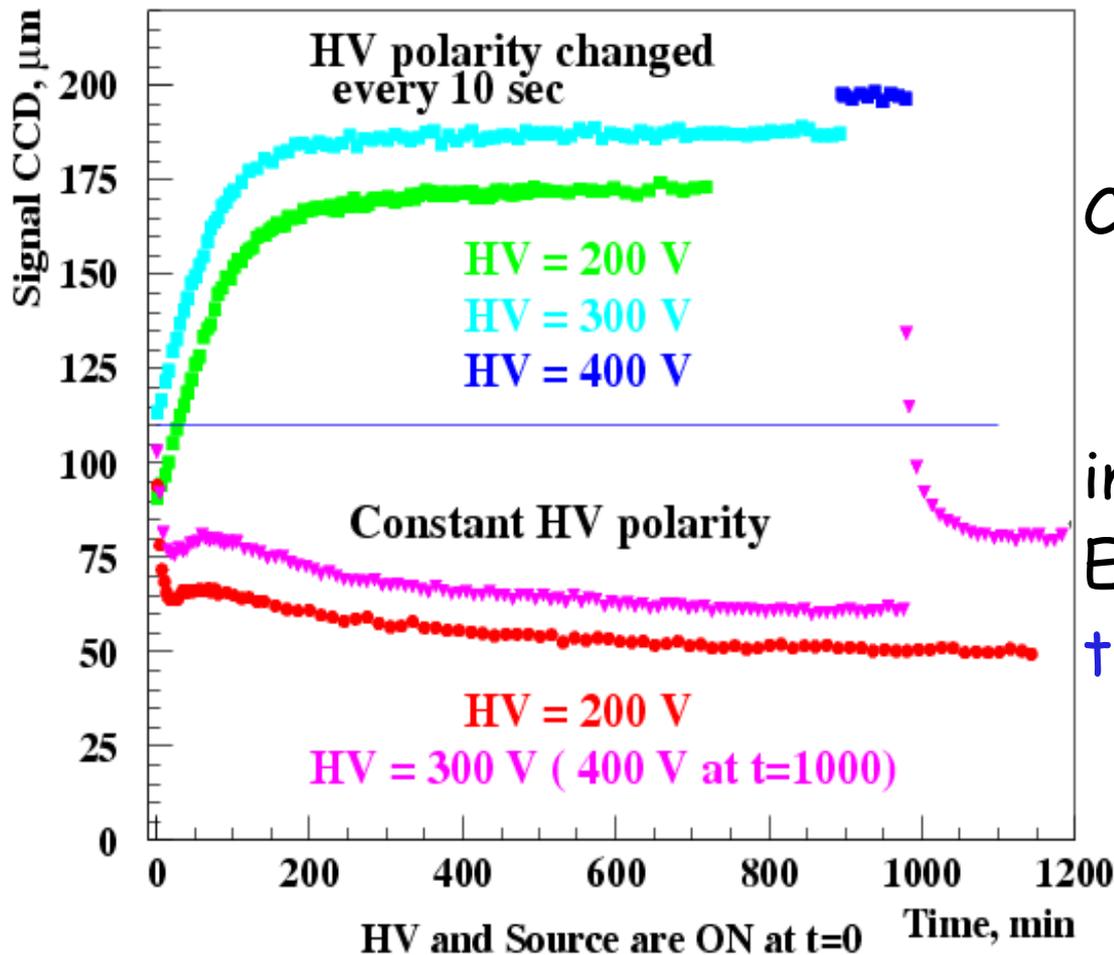


Trigger rate  
about 12 Hz,  
old trigger  
counters,  
 $h_{\text{Source}} \sim 36 \text{ mm}$



# CCD vs time, different HV

So14-04 Diamond Sample (5 MGy)



"High rate" data

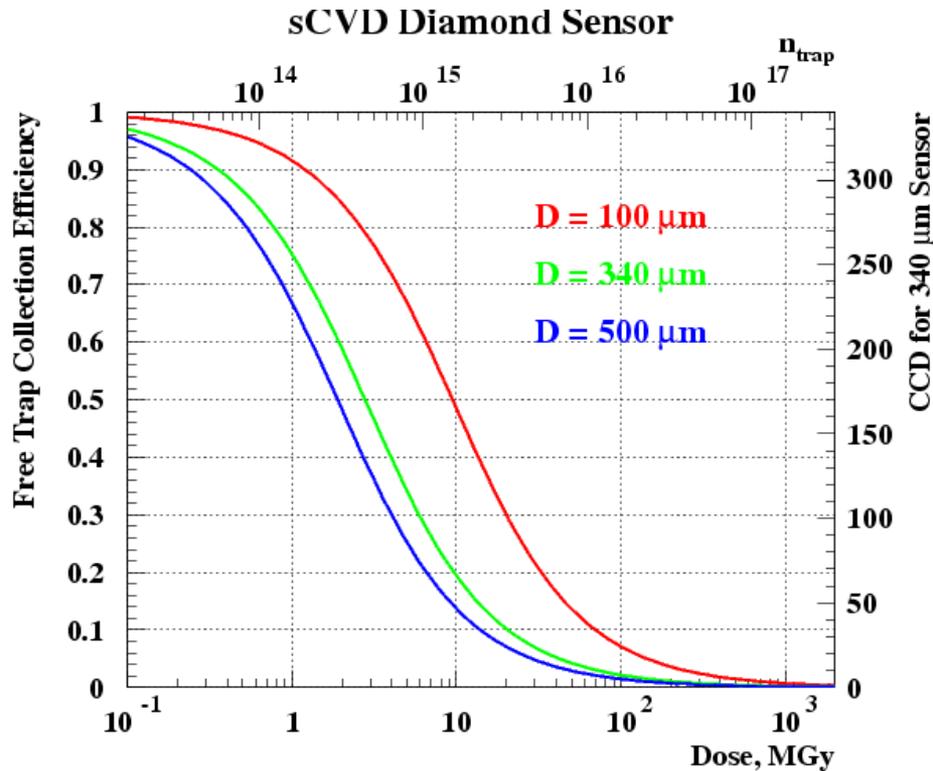
CCD dependence on HV in case of switching polarity is **NOT** yet in the model. What is E-field dependent: trap release time, capture probability?



Charge absorption probability for the thin layer:

$$P_l = 1 - \exp\left(-\pi R_{trap}^2 \cdot \frac{l}{l_0} \cdot \frac{n_{free}}{N}\right) = 1 - e^{-al}$$

$$a = \frac{\pi R_{trap}^2}{l_0} \cdot \frac{n_{free}}{N}$$



In case when free traps are uniformly distributed:

Charge collection efficiency could be calculated analytically. For the detector of thickness  $D$ :

$$CCE_0 = \frac{2}{aD} \cdot \left(1 - \frac{1 - \exp(-aD)}{aD}\right)$$

- Strong polarization effect is observed in the radiation damaged scCVD Diamond detector.
- It was shown that the polarization significantly decreases the detector charge collection efficiency.
- A simple model is developed in order to understand and describe observed phenomena.
- Method of routinely switching HV polarity is proposed to suppress polarization. Large improvement of CCE is observed experimentally.
- More work is needed to understand CCD dependence on the signal rate and details of polarization development.
- It is desirable to continue test beam studies up to higher doses (approx 50 MGy) and measure sensor CCD @ ILC-like conditions.

Thank you...

Special thanks to GSI team:  
CVDD sensors, test beam etc.



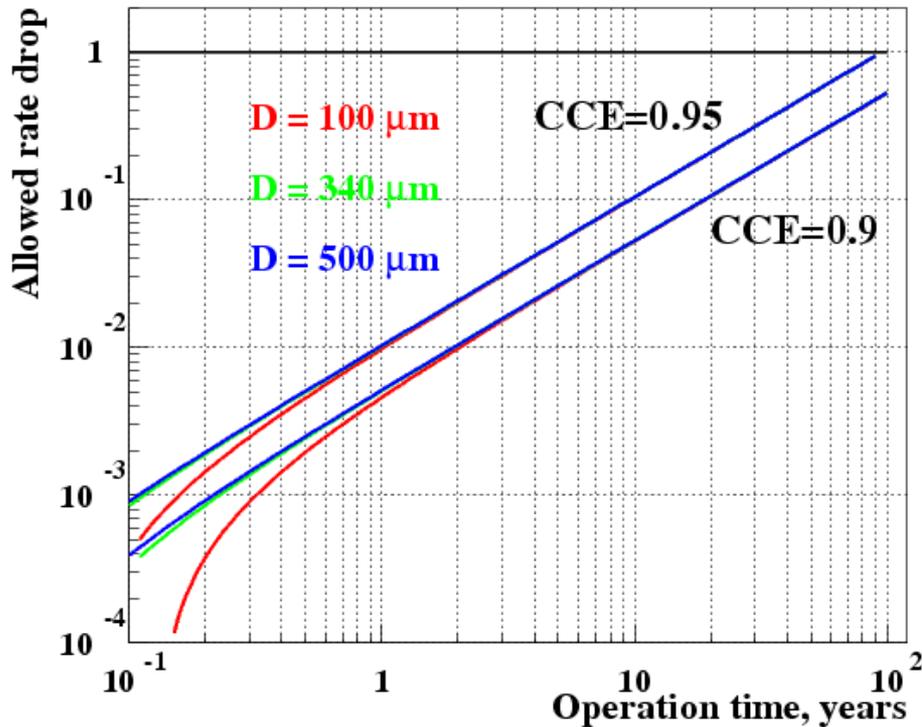
# Uniformly (partly) filled traps

Allowed reduction of the flux keeping  $\epsilon$  efficiency:

$$r = \frac{\Phi_{\epsilon}}{\Phi_{nom}} = \frac{1}{R_{nom}^q} \cdot \frac{Q}{T_0 \cdot Q_{absorb}} \cdot \left( t - \frac{n_{free}^{\epsilon}}{R_{trap}} \right)$$

; t – detector operation time

sCVD Diamond Sensor



Alternating HV polarity +  
+ stable particle flux =  
= XXL radiation hardness

Charge collection efficiency  
could be kept at high level  
for a very long time if particle  
flux is maintained stable.

Leakage current ???  
Crystal destruction ???